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Team Nexperia



PMN27UP

20 V, 5.7 A P-channel Trench MOSFET Rev. 1 — 13 July 2011

Product data sheet

Product profile

1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- 1.8 V R_{DSon} rated
- Very fast switching

Trench MOSFET technology

1.3 Applications

- Relay driver
- High-speed line driver

- High-side load switch
- Switching circuits

1.4 Quick reference data

Table 1. **Quick reference data**

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	-20	V
V_{GS}	gate-source voltage			-8	-	8	V
I _D	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 ^{\circ}\text{C}$	<u>[1]</u>	-	-	-5.7	Α
Static charact	eristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = -4.5 \text{ V}; I_D = -2.4 \text{ A}; T_j = 25 \text{ °C}$		-	27	32	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

Pinning information

Table 2. **Pinning information**

	•			
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	D. D. D.	5
2	D	drain	<u> </u>	
3	G	gate		
4	S	source	1 1 2 13	
5	D	drain	SOT457 (TSOP6)	Ś
6	D	drain		017aaa094



20 V, 5.7 A P-channel Trench MOSFET

3. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PMN27UP	TSOP6	plastic surface-mounted package (TSOP6); 6 leads	SOT457		

4. Marking

Table 4. Marking codes

Type number	Marking code
PMN27UP	ZU

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-20	V
V_{GS}	gate-source voltage			-8	8	V
I _D	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C}$	<u>[1]</u>	-	-5.7	Α
		$V_{GS} = -4.5 \text{ V}; T_{amb} = 100 ^{\circ}\text{C}$	<u>[1]</u>	-	-3.5	Α
I _{DM}	peak drain current	$T_{amb} = 25 \text{ °C}$; single pulse; $t_p \le 10 \text{ µs}$		-	-23	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	540	mW
			<u>[1]</u>	-	1385	mW
		T _{sp} = 25 °C		-	6250	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drai	in diode					
Is	source current	T _{amb} = 25 °C	<u>[1]</u>	-	-1.5	Α

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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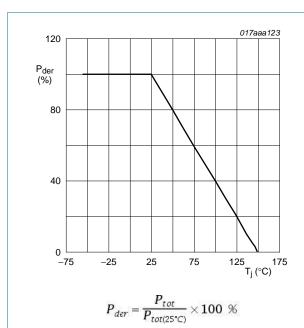


Fig 1. Normalized total power dissipation as a function of junction temperature

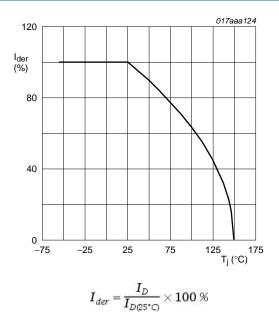
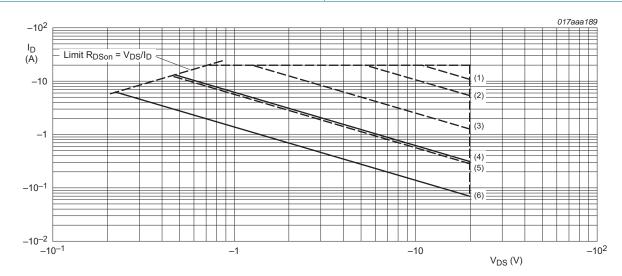


Fig 2. Normalized continuous drain current as a function of junction temperature



I_{DM} = single pulse

(1)
$$t_p = 100 \, \mu s$$

(2)
$$t_p = 1 \text{ ms}$$

(3)
$$t_p = 10 \text{ ms}$$

(4) DC;
$$T_{sp} = 25$$
 °C

(5)
$$t_p = 100 \text{ ms}$$

(6) DC; $T_{amb} = 25 \, ^{\circ}\text{C}$; drain mounting pad 6 cm²

Fig 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

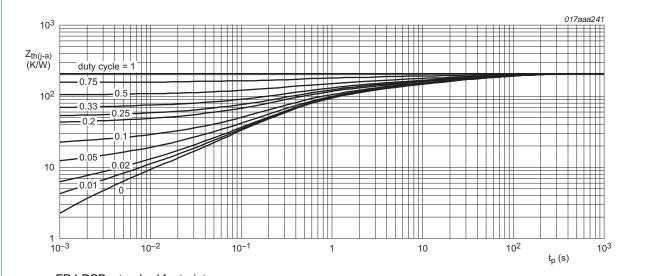
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6. Thermal characteristics

Table 6. Thermal characteristics

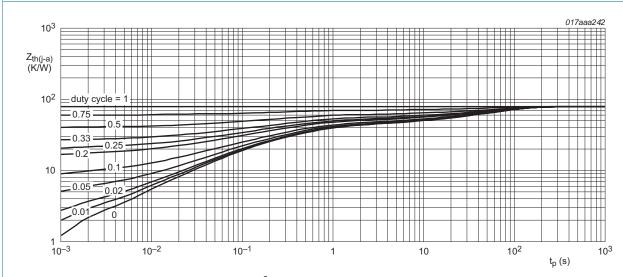
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u>	-	200	230	K/W
			[2]	-	78	90	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	12	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².



FR4 PCB, standard footprint

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 6 cm²

Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

PMN27UP

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7. Characteristics

Table 7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-20	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	-0.45	-0.7	-0.95	V
I _{DSS}	drain leakage current	$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μΑ
		$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 ^{\circ}\text{C}$	-	-	-10	μΑ
I _{GSS}	gate leakage current	$V_{GS} = -8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-100	nΑ
Doon	drain-source on-state	$V_{GS} = -4.5 \text{ V}; I_D = -2.4 \text{ A}; T_j = 25 \text{ °C}$	-	27	32	mΩ
	resistance	$V_{GS} = -4.5 \text{ V}; I_D = -2.4 \text{ A}; T_j = 150 \text{ °C}$	-	41	48	mΩ
		$V_{GS} = -2.5 \text{ V}; I_D = -2.0 \text{ A}; T_j = 25 \text{ °C}$	-	36	41	mΩ
		$V_{GS} = -1.8 \text{ V}; I_D = -1.8 \text{ A}; T_j = 25 \text{ °C}$	-	57	66	mΩ
9 _{fs}	forward transconductance	$V_{DS} = -5 \text{ V}; I_D = -2.4 \text{ A}; T_j = 25 \text{ °C}$	-	14	-	S
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$V_{DS} = -10 \text{ V}; I_D = -1 \text{ A}; V_{GS} = -4.5 \text{ V};$	-	21	31	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	4.2	-	nC
Q_{GD}	gate-drain charge		-	2.8	-	nC
C _{iss}	input capacitance	$V_{DS} = -10 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$	-	2340	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	210	-	pF
C _{rss}	reverse transfer capacitance		-	150	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -10 V; V_{GS} = -4.5 V; $R_{G(ext)}$ = 6 Ω ;	-	19	-	ns
t _r	rise time	$T_j = 25 ^{\circ}\text{C}; I_D = -1 ^{\circ}\text{A}$	-	20	-	ns
t _{d(off)}	turn-off delay time		-	95	-	ns
t _f	fall time		-	27	-	ns
Source-d	rain diode					
V_{SD}	source-drain voltage	$I_S = -2.4 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_i = 25 \text{ °C}$	-	-0.75	-1	V

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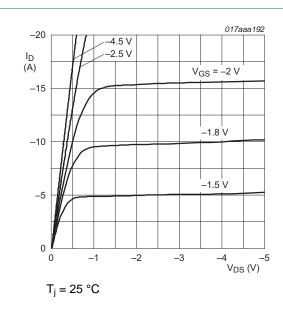
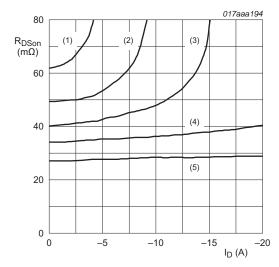


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values



 $T_i = 25 \, ^{\circ}C$

(1) $V_{GS} = -1.5 \text{ V}$

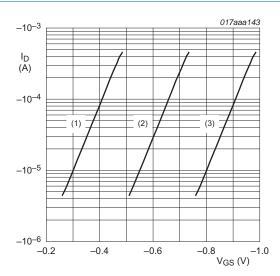
(2) $V_{GS} = -1.8 \text{ V}$

(3) $V_{GS} = -2.0 \text{ V}$

(4) $V_{GS} = -2.5 \text{ V}$

(5) $V_{GS} = -4.5 \text{ V}$

Fig 8. Drain-source on-state resistance as a function of drain current; typical values



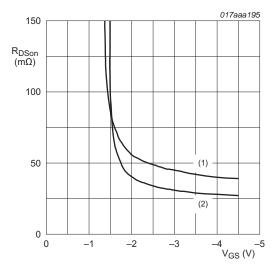
 $T_{j} = 25 \, ^{\circ}\text{C}; \, V_{DS} = -3 \, \text{V}$

(1) minimum values

(2) typical values

(3) maximum values

Fig 7. Sub-threshold drain current as a function of gate-source voltage



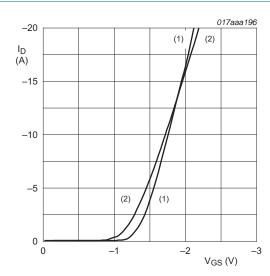
 $I_D = -2.4 A$

(1) $T_i = 150 \, ^{\circ}C$

(2) $T_j = 25 \, ^{\circ}C$

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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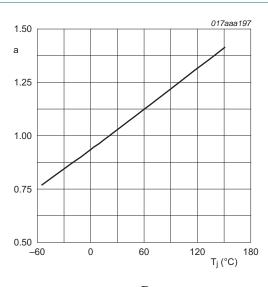


 $V_{DS} > I_D \times R_{DSon}$

(1)
$$T_j = 25 \, ^{\circ}C$$

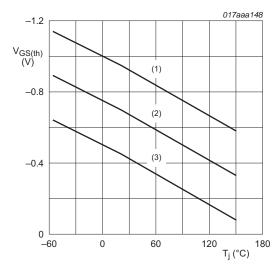
(2)
$$T_i = 150 \, ^{\circ}\text{C}$$

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

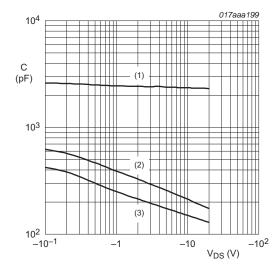
Fig 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values



 I_D = -0.25 mA; V_{DS} = V_{GS}

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

- (1) C_{iss}
- (2) C_{oss}
- (3) C_{rss}

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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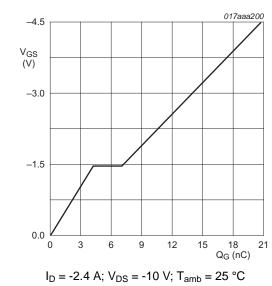


Fig 14. Gate-source voltage as a function of gate charge; typical values

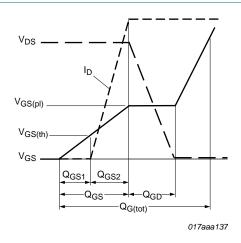
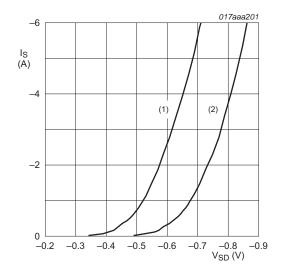


Fig 15. Gate charge waveform definitions



 $V_{GS} = 0 V$

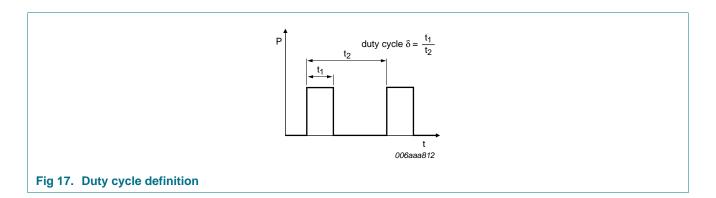
(1) $T_j = 150 \, ^{\circ}\text{C}$

(2) $T_i = 25 \, ^{\circ}C$

Fig 16. Source current as a function of source-drain voltage; typical values

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8. Test information



20 V, 5.7 A P-channel Trench MOSFET

9. Package outline

Plastic surface-mounted package (TSOP6); 6 leads

SOT457

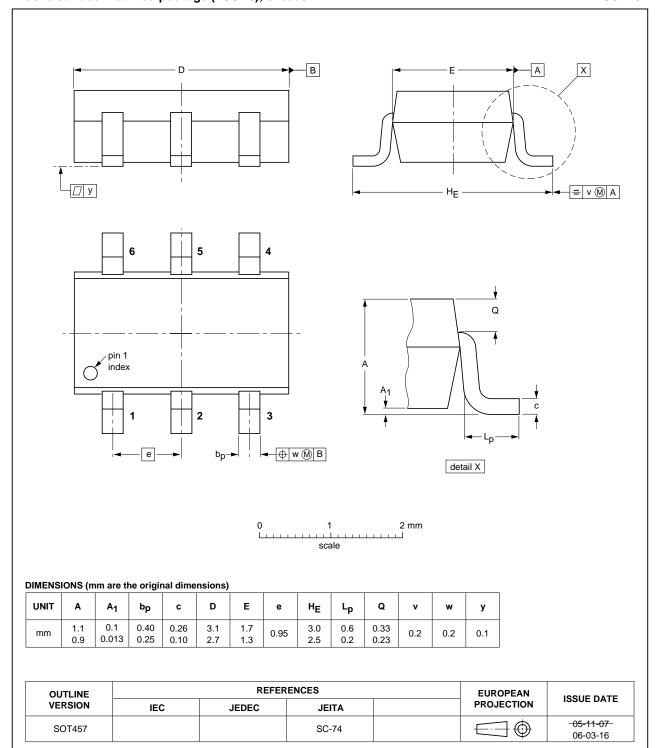
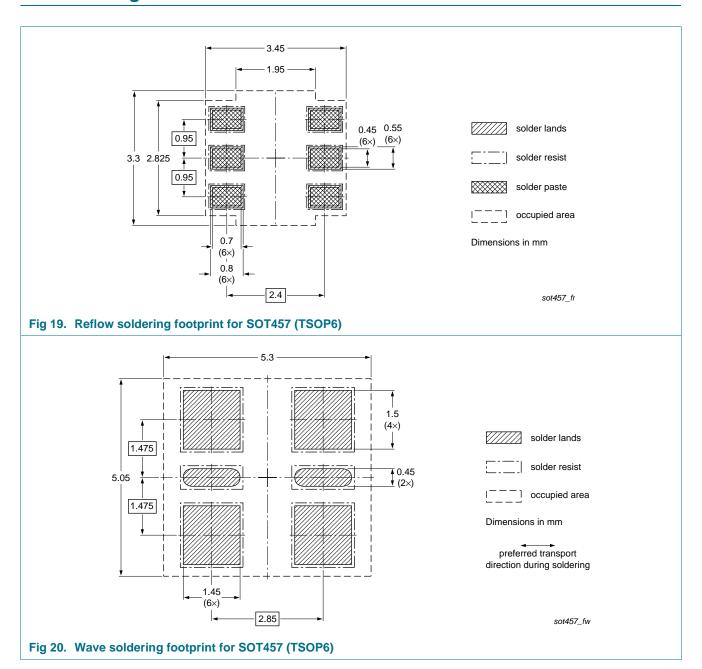


Fig 18. Package outline SOT457 (TSOP6)

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10. Soldering



20 V, 5.7 A P-channel Trench MOSFET

11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMN27UP v.1	20110713	Product data sheet	-	-

20 V, 5.7 A P-channel Trench MOSFET

12. Legal information

12.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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